Automotive Body Power Management LSI

LDO Regulator BD357XFP/HFP SERIES

TENTATIVE ROHM CO.,LTD

DESIGN INFORMATION

Description

BD357XFP/HFP SERIES regulators feature a high 50 V withstand-voltage and are suitable for use with onboard vehicle microcontrollers. They offer the output current of 500 mA while limiting the quiescent current to $30 \,\mu$ A (TYP). With these devices, a ceramic capacitor can be selected at the output for stable operation, the output tolerance is within $\pm 2\%$ over the wide ambient temperature range (-40 to 125°C), and the short circuit protection is folded-type to minimize generation of heat during malfunction. These devices are developed to offer most robust power-supply design under the harsh automotive environment. The BD357XFP/HFP Series provide ideal solutions to lower the current consumption as well as to simplify the use with battery direct-coupled systems.

Features

- 1) Ultra-low quiescent current: $30 \mu A$ (TYP.)
- 2) Low-saturation voltage type P-channel DMOS output transistors
- 3) High output voltage precision: $\pm 2\%$ /lomax = 500 mA
- 4) Low-ESR ceramic capacitors can be used as output capacitors.
- 5) Vcc power supply voltage = 50 V
- 6) Built-in overcurrent protection circuit and thermal shutdown circuit
- 7) TO252-3,5/HRP-5 Package

Applications

· Onboard vehicle devices (body-control, car stereos, satellite navigation systems, etc.)

Product line

	BD3570FP/HFP	BD3571FP/HFP	BD3572FP/HFP	BD3573FP/HFP	BD3574FP/HFP	BD3575FP/HFP
Output voltage	3.3V	5.0 V	Variable	3.3V	5.0 V	Variable
SW function	—	—	—	0	0	0
Package	FP:TO252-3,TO2	252-5				

FP:TO252-3,TO252-5 HFP:HRP5

Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limit	Unit
Supply voltage	Vcc	50 ※1	V
Switch Supply voltage	Vsw	50 %2	V
Output current	lo	500	mA
		1.2 (TO252-3) ※3	
Power dissipation	Pd	1.3 (TO252-5) ※4	W
		1.6 (HRP5) ※5	
Operating temperature range	Topr	-40 to +125	°C
Storage temperature range	Tstg	-55 to +150	°C
Maximum junction temperature	Tjmax	150	°C

%1 Not to exceed Pd and ASO.

%2 for ON/OFF SW Regulator only

3 TO252-3: Reduced by 9.6 mW/°C over 25 °C, when mounted on a glass epoxy board (70 mm \times 70 mm \times 1.6 mm).

 $\%5 \quad \text{HRP-5: Reduced by 12.8 mW/°C over 25 °C, when mounted on a glass epoxy board (70 mm <math display="inline">\times$ 70 mm \times 1.6 mm).}







•Operating Conditions

	Symbol	Min.	Max.	Unit	
Input voltogo	BD3570,3572,3573,3575FP/HFP	Vcc	4.5 ※6	36.0	V
Input voltage	BD3571,3574FP/HFP	Vcc	5.5 %6	36.0	V
	lo	-	500	mA	
Variat	Vo	2.8	12	V	

%6 Please consider that the Output voltage would be dropped (Dropout voltage) according to the output current.

●Electrical Characteristics (Unless otherwise specified, Ta=-40 to125°C, Vcc=13.2 V, SW=3V ※7, Vo settings is 5V ※8)

Parameter	Symbol	Limit		Unit	Conditions	
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Shut Down Current ※ 7	lshut	_	_	10	μA	SW=GND
Bias current	lb	_	30	50	μA	Io=0mA
Output voltage	Vo	Vo× 0.98	Vo	Vo× 1.02	V	Io=200mA, Vo:Please refer to Product line.
ADJ Terminal voltage ※8	VADJ	1.235	1.260	1.285	V	Io=200mA
Output current	lo	0.5	_	_	A	
Dropout voltage	riangle Vd	_	0.25	0.48	V	Vcc=4.75V,Io=200mA
Ripple rejection	R.R.	45	55	_	dB	f=120Hz,ein=1Vrms,IO=100mA
Line Regulation	Reg.I	_	10	30	mV	$VCCD \approx 10 \leq VCC \leq 25V$ IO = 0 mA
Load Regulation	Reg.L	_	20	40	mV	0mA≦lo≦200mA
Swith Threshold voltage H ※ 7	SWH	2.0	_	_	V	Io=0 mA
Swith Threshold voltage L ※ 7	SWL	_	_	0.5	V	Io=0 mA
Swith Bias current	SWI	_	22	60	μA	SW=5V,Io=0mA

%7 BD3573,3574,3575FP/HFP only

%8 BD3572,3575FP/HFP only

%9 BD3571,3572,3574,3575FP/HFP only

%10 BD3570,3573FP/HFP :Vccd=5.5V

BD3571,3572,3574,3575FP/HFP :VccD=6.5V

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Ta=25℃

1500

Ta=25℃

Ta=-40℃

2

120

1.5

2000

Ta=125℃

1000

500

0.5

0

40

Temperature

80

1

SUPPLY VOLTAGE: Vsw [V]

SW Input Voltage

●Reference Data: BD3574HFP (Unless otherwise specified, Ta=25°C)

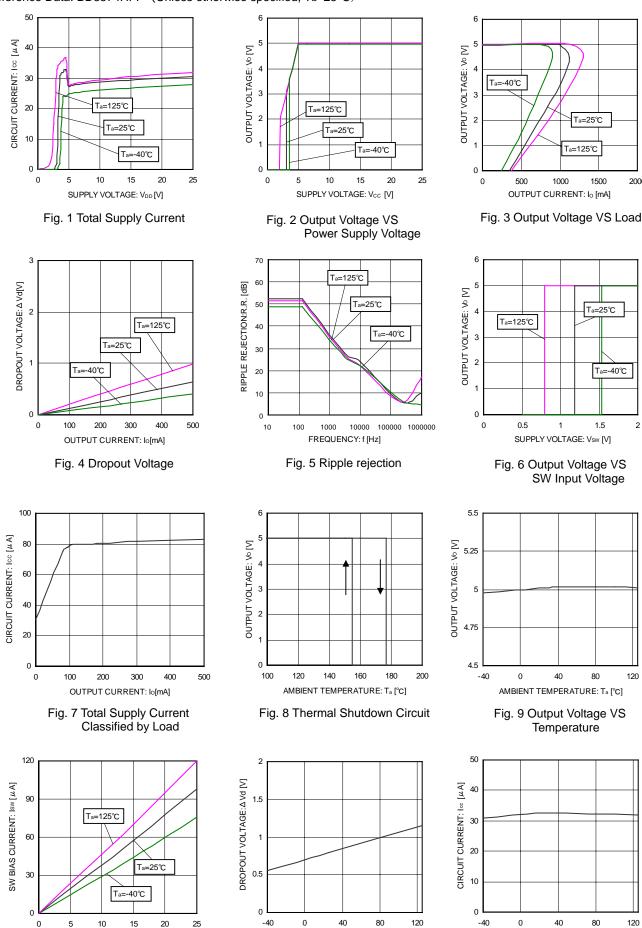


Fig. 11 Dropout voltage VS Temperature

AMBIENT TEMPERATURE: Ta [°C]

Fig. 12 Total Supply Current Temperature

40

AMBIENT TEMPERATURE: Ta [°C]

80

120

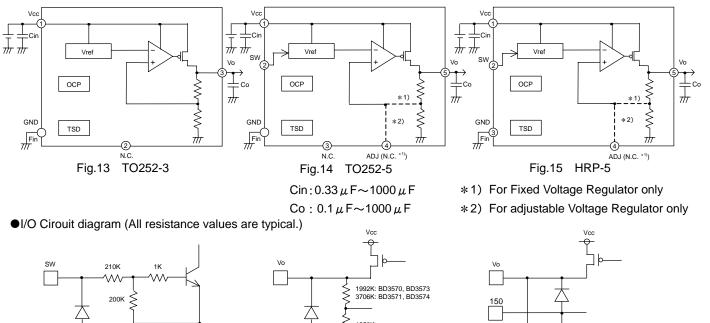
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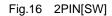
SUPPLY VOLTAGE: Vsw [V]

Fig. 10 SW Bias current

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Block Diagram





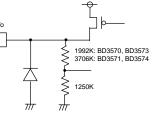
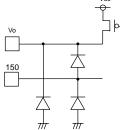


Fig.17 5PIN[Vo] BD3570,3571,3573,3574



4.5PIN[ADJ,Vo] Fig.18 BD3572,BD3575

Pin Assignments

•TO252-3

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	Ο	
Η		Η
П		П
1	2	3

FIN

 π

Pin No.	Pin name	Function
1	Vcc	Power supply pin
2	N.C.	N.C. pin
3	Vo	Voltage output pin
Fin	GND	GND pin

Fig.	19
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FIN

Ο BBBBB 12345

Fig.20

Fig. 21

•TO252-5

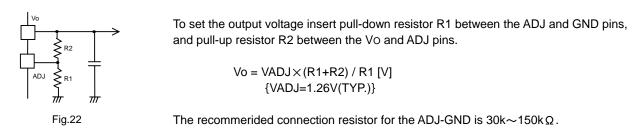
Pin No.	Pin name	Function
1	Vcc	Power supply pin
2	SW	Vo ON/OFF function pin
2	N.C.	N.C. pin(BD3572FP only)
3	N.C.	N.C. pin
4	N.C.	N.C. pin
4	ADJ	Output voltage setting pin(BD3572,3575FP only)
5	Vo	Voltage output pin
Fin	GND	GND pin

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•HRP-5	\bigcirc
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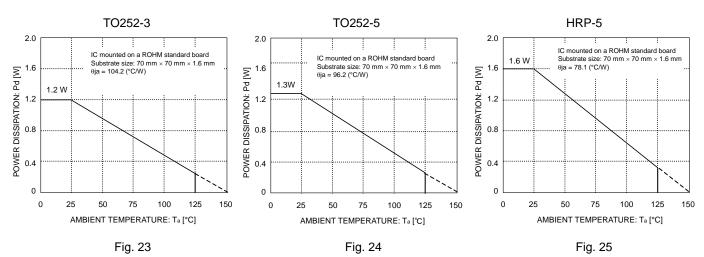
Pin No.	Pin name	Function
1	Vcc	Power supply pin
2	SW	Vo ON/OFF function pin (BD3573,3574,3575HFP only)
2	N.C.	N.C. pin
3	GND	GND pin
4	N.C.	N.C. pin
4	ADJ	Output voltage setting pin(BD3572,3575HFP only)
5	Vo	Voltage output pin
Fin	GND	GND pin

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Output Voltage Adjustment



Setting of Heat



Refer to the heat mitigation characteristics illustrated in Figs. 17 and 18 when using the IC in an environment where $T_a \ge 25^{\circ}$ C. The characteristics of the IC are greatly influenced by the operating temperature. If the temperature is in excess of the maximum junction temperature T_{jmax} , the elements of the IC may be deteriorated or damaged. It is necessary to give sufficient consideration to the heat of the IC in view of two points, i.e., the protection of the IC from instantaneous damage and the

maintenance of the reliability of the IC in long-time operation. In order to protect the IC from thermal destruction, it is necessary to operate the IC not in excess of the maximum junction temperature T_{jmax}. Fig. 17 illustrates the power dissipation/heat mitigation characteristics for the TO252 package. Operate the IC within the power dissipation Pd. The following method is used to calculate the power consumption Pc (W).

	Vcc : Input voltage
Pc=(Vcc-Vo)×Io+Vcc×Icc	Vo : Output voltage
Power dissipation Pd≦Pc	lo : Load current
	Icc : Total supply current

The load current Io is obtained to operate the IC within the power dissipation.

 $Io \leq \frac{Pd-Vcc \times Icc}{Vcc-Vo}$ (For more information about Icc, see page 12.)

The maximum load current lomax for the applied voltage Vcc can be calculated during the thermal design process.

•Calculation example

Example: BD3571FP Vcc = 12 V and Vo = 5 V at Ta = 85°C

$$lo \leq \frac{0.624 \cdot 12 \times lcc}{12 \cdot 5} \qquad \qquad \left(\begin{array}{c} \theta \text{ ja} = 104.2^{\circ}\text{C/W} \rightarrow -9.6\text{mAW/}^{\circ}\text{C} \\ 25^{\circ}\text{C} = 1.2\text{W} \rightarrow 85^{\circ}\text{C} = 0.624\text{W} \end{array} \right)$$

Make a thermal calculation in consideration of the above so that the whole operating temperature range will be within the power dissipation.

The power consumption Pc of the IC in the event of shorting (i.e., if the Vo and GND pins are shorted) will be obtained from the following equation.

Pc=Vcc×(lcc+lshort) Ishort = Short current

•Peripheral Settings for Pins and Precautions



1) Vcc pins

Insert capacitors with a capacitance of 0.33 μ F to 1000 μ F between the Vcc and GND pins.

The capacitance varies with the application. Be sure to design the capacitance with a sufficient margin.

2) Capacitors for stopping oscillation for output pins

Capacitors for stopping oscillation must be placed between each output pin and the GND pin. Use a capacitor within a capacitance range between $0.1 \,\mu$ F and $1000 \,\mu$ F. Since oscillation does not occur even for ESR values from $0.001 \,\Omega$ to $100 \,\Omega$, a ceramic capacitor can be used. Abrupt input voltage and load fluctuations can affect output voltages. Output capacitor capacitance values should be determined after sufficient testing of the actual application.

Operation Notes

1) Absolute maximum ratings

Use of the IC in excess of absolute maximum ratings such as the applied voltage or operating temperature range may result in IC damage. Assumptions should not be made regarding the state of the IC (short mode or open mode) when such damage is suffered. A physical safety measure such as a fuse should be implemented when use of the IC in a special mode where the absolute maximum ratings may be exceeded is anticipated.

2) GND potential

Ensure a minimum GND pin potential in all operating conditions.

3) Setting of heat

Use a thermal design that allows for a sufficient margin in light of the power dissipation (Pd) in actual operating conditions.

4) Pin short and mistake fitting

Use caution when orienting and positioning the IC for mounting on printed circuit boards. Improper mounting may result in damage to the IC. Shorts between output pins or between output pins and the power supply and GND pins caused by the presence of a foreign object may result in damage to the IC.

5) Actions in strong magnetic field

Use caution when using the IC in the presence of a strong magnetic field as doing so may cause the IC to malfunction.

6) Testing on application boards

When testing the IC on an application board, connecting a capacitor to a pin with low impedance subjects the IC to stress. Always discharge capacitors after each process or step. Be sure to turn power off when mounting or dismounting jigs at the inspection stage. Furthermore, for countermeasures against static electricity, ground the equipment at the assembling stage and pay utmost attention at the time of transportation or storing the product.

- 7) This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. PN junction is formed by the P layer and the N layer of each element, and a variety of parasitic elements will be constituted. For example, when a resistor and transistor are connected to pins as shown in Fig. 19,
 - the P/N junction functions as a parasitic diode when GND>Pin A for the resistor or GND>Pin B for the transistor (NPN).
 - Similarly, when GND>Pin B for the transistor (NPN), the parasitic diode described above combines with the N layer of other adjacent elements to operate as a parasitic NPN transistor.

The formation of parasitic elements as a result of the relationships of the potentials of different pins is an inevitable result of the IC's architecture. The operation of parasitic elements can cause interference with circuit operation as well as IC malfunction and damage. For these reasons, it is necessary to use caution so that the IC is not used in a way that will trigger the operation of parasitic elements, such as by the application of voltages lower than the GND (P substrate) voltage to input pins.

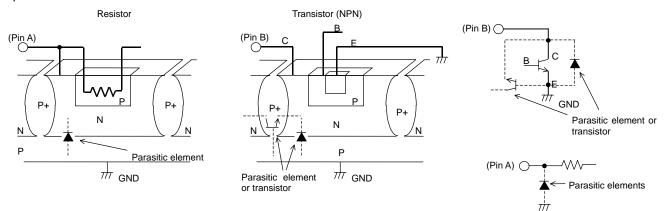


Fig. 26 Example of a Simple Monolithic IC Architecture

8) Ground wiring patterns

When using both small signal and large current GND patterns, it is recommended to isolate the two ground patterns, placing a single ground point at the application's reference point so that the pattern wiring resistance and voltage variations caused by large currents do not cause variations in the small signal ground voltage. Be careful not to change the GND wiring pattern of any external parts, either.

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9) SW Pin

Do not apply the voltage to SW pin when the Vcc is not applied. And when the Vcc is applied, the voltage of SW pin must not exceed Vcc.

10) Thermal shutdown circuit (TSD)

This IC incorporates a built-in thermal shutdown circuit for the protection from thermal destruction. The IC should be used within the specified power dissipation range. However, in the event that the IC continues to be operated in excess of its power dissipation limits, the attendant rise in the chip's temperature T_j will trigger the thermal shutdown circuit to turn off all output power elements. The circuit automatically resets once the chip's temperature T_j drops.

The thermal shutdown circuit operates if the IC is under conditions in express of the absolute maximum ratings. Never design sets on the premise of using the thermal shutdown circuit. (See Fig. 8)

11) Overcurrent protection circuit (OCP)

The IC incorporates a built-in overcurrent protection circuit that operates according to the output current capacity. This circuit serves to protect the IC from damage when the load is shorted. The protection circuit is designed to limit current flow by not latching in the event of a large and instantaneous current flow originating from a large capacitor or other component. These protection circuits are effective in preventing damage due to sudden and unexpected accidents. However, the IC should not be used in applications characterized by the continuous operation or transitioning of the protection circuits. At the time of thermal designing, keep in mind that the current capability has negative characteristics to temperatures. (See Fig. 3)

•Selecting a Model Name When Ordering

